

1.

The 30N06 is the highest performance trench N-ch MOSFETs with extreme high cell density, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications. The 30N06 meet the RoHS and Green Product requirement, 100%EAS guaranteed with full function reliability approved.

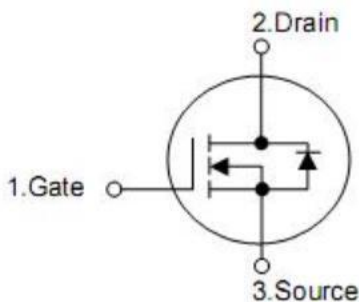
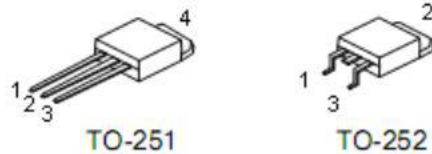
2.

- R<sub>DS(on)</sub>=25mΩ @ V<sub>DS</sub>=60V
- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent C<sub>dv/dt</sub> effect decline
- 100%EAS Guaranteed
- Green Device Available

3.

- High Frequency Point-of-Load Synchronous Buck Converter
- Networking DC-DC Power System
- Load Switch

4.



Pin	Function
1	Gate
2	Drain
3	Source
4	Drain

## 5. Absolute maximum ratings

Parameter	Symbol	Rating	Units	
Drain-source voltage	$V_{DS}$	60	V	
Gate-source voltage	$V_{GS}$	+20	V	
Continuous drain current, $V_{GS} @ 10V_1$	$I_D$	$T_C=25^{\circ}C$	25	A
		$T_C=100^{\circ}C$	18	A
Pulsed drain current <sup>2</sup>	$I_{DM}$	50	A	
Single pulse avalanche energy <sup>3</sup>	$E_{AS}$	34.5	mJ	
Avalanche current	$I_{AS}$	22.6	A	
Total power dissipation <sup>4</sup>	$P_D$	34.7	W	
Operation junction temperature range	$T_J$	-55 to 150	$^{\circ}C$	
Storage temperature range	$T_{STG}$	-55 to 150	$^{\circ}C$	

## 6. Thermal characteristics

Parameter	Symbol	Typ	Max	Unit
Thermal resistance, Junction-ambient <sup>1</sup>	$R_{\theta JA}$	--	62	$^{\circ}C/W$
Thermal resistance, Junction-case <sup>1</sup>	$R_{\theta JC}$	--	3.6	

## 7. Electrical characteristics

(T<sub>J</sub>=25°C, unless otherwise noted)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Units
Drain-source breakdown voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =250μA	60	-	-	V
BV <sub>DSS</sub> temperature coefficient	ΔBV <sub>DSS</sub> /ΔT <sub>J</sub>	Reference to 25 °C, I <sub>D</sub> =1mA		0.063		V/°C
Static drain-source on-resistance <sup>2</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =15A		25	30	mΩ
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =10A		30	38	
Gate threshold voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA	1.2		2.5	V
V <sub>GS(th)</sub> temperature coefficient	ΔV <sub>GS(th)</sub>			-5.24		mV/°C
Drain-source leakage current	I <sub>DSS</sub>	V <sub>DS</sub> =48V, V <sub>GS</sub> =0V T <sub>J</sub> =25°C			1	μA
		V <sub>DS</sub> =48V, V <sub>GS</sub> =0V T <sub>J</sub> =55°C			5	μA
Gate- source leakage current	I <sub>GSS</sub>	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V			±100	nA
Forward transconductance	g <sub>fs</sub>	V <sub>DS</sub> =5V, I <sub>D</sub> =15A		17		S
Gate resistance	R <sub>g</sub>	V <sub>DS</sub> =0V, V <sub>GS</sub> =0V, f=1MHz		3.2		Ω
Total gate charge(4.5V)	Q <sub>g</sub>	V <sub>DS</sub> =48V, V <sub>GS</sub> =4.5V I <sub>D</sub> = 10A	-	12.56		nC
Gate-source charge	Q <sub>gs</sub>			3.24		
Gate-drain charge	Q <sub>gd</sub>			6.31		
Turn-on delay time	t <sub>d(on)</sub>	V <sub>DD</sub> =30V, I <sub>D</sub> =10A, R <sub>G</sub> =3.3Ω, V <sub>GS</sub> =10V		8		ns
Rise time	t <sub>r</sub>			14.2		
Turn-off delay time	t <sub>d(off)</sub>			24.4		
Fall time	t <sub>f</sub>			4.6		
Input capacitance	C <sub>iss</sub>	V <sub>DS</sub> =25V, V <sub>GS</sub> =0V, f=1MHz		1345		pF
Output capacitance	C <sub>oss</sub>			72.5		
Reverse transfer capacitance	C <sub>rss</sub>			54.4		
Single pulse avalanche energy <sup>5</sup>	EAS	V <sub>DD</sub> =25V, L=0.1mH, I <sub>AS</sub> =15A	15.2			mJ
Continuous source current <sup>1,6</sup>	I <sub>S</sub>	V <sub>G</sub> = V <sub>D</sub> =0V, Force current			25	A
Pulsed source current <sup>2,6</sup>	I <sub>SM</sub>				50	A
Diode forward voltage <sup>2</sup>	V <sub>SD</sub>	V <sub>GS</sub> =0V, I <sub>S</sub> =1A, T <sub>J</sub> =25°C			1.2	V

Note:1.The data tested by surface mounted on a 1 inch<sup>2</sup> FR-4 board with 20Z copper.

2.The data tested by pulsed, pulse width<300μs,duty cycle<2%

3.The EAS data shows Max.rating.The test condition is V<sub>DD</sub>=25V, V<sub>GS</sub>=10V,L=0.1mH,I<sub>AS</sub>=15A

4.The power dissipation is limited by 150°C junction temperature

5.The Min, value is 100% EAS tested guarantee.

6.The data is theoretically the same as I<sub>D</sub> and I<sub>DM</sub>,in real applications, should be limited by total power dissipation.

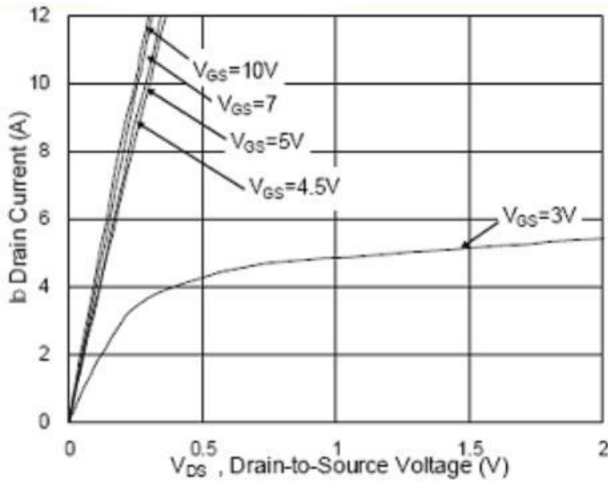


Fig.1 Typical Output Characteristics

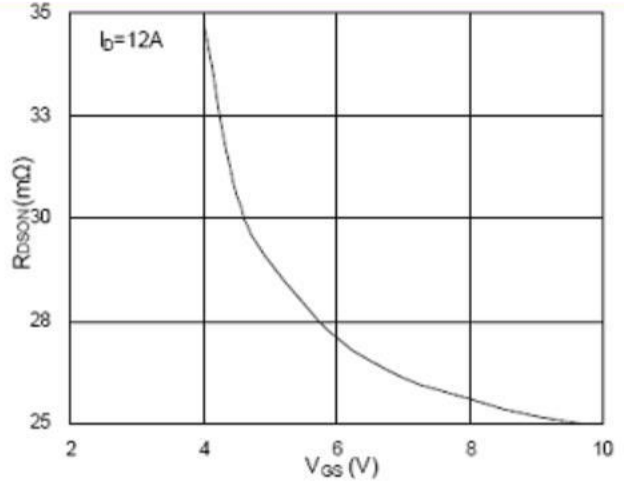


Fig.2 On-Resistance v.s Gate-Source.

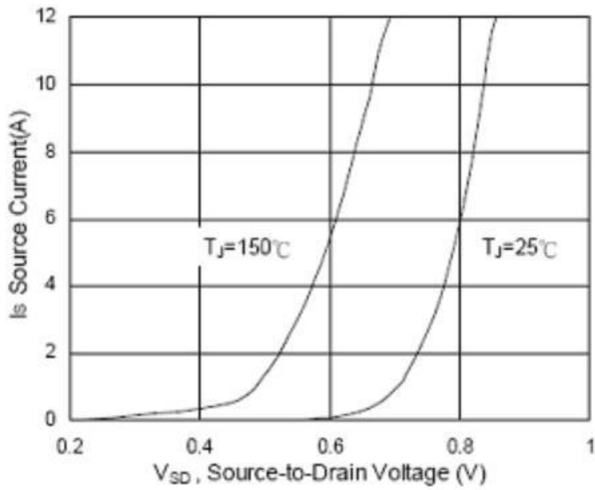


Fig.3 Forward Characteristics of Reverse

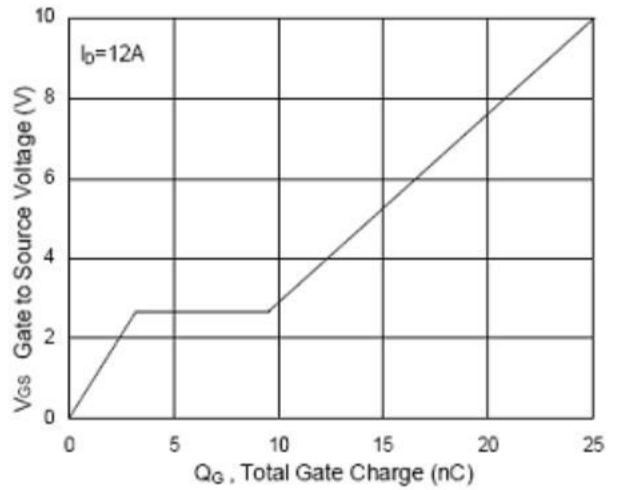


Fig.4 Gate-Charge characteristics

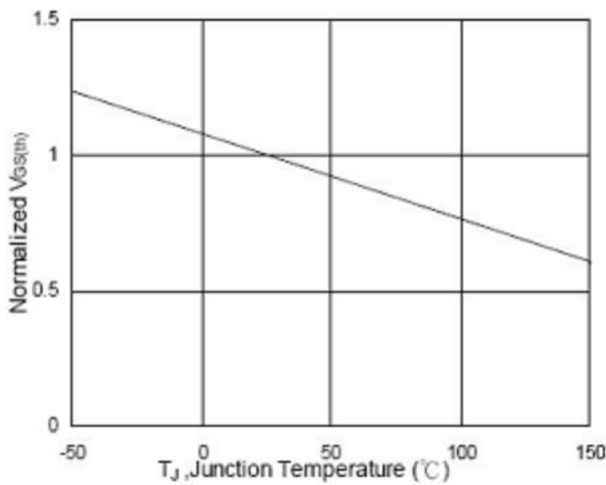


Fig.5 Normalized  $V_{GS(th)}$  v.s  $T_J$

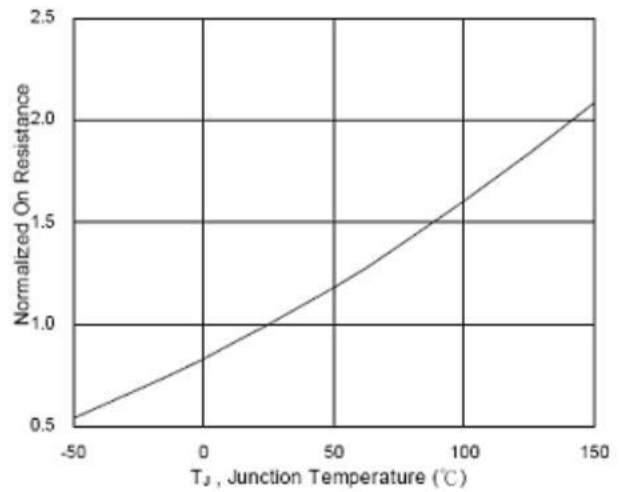


Fig.6 Normalized  $R_{DS(on)}$  v.s  $T_J$

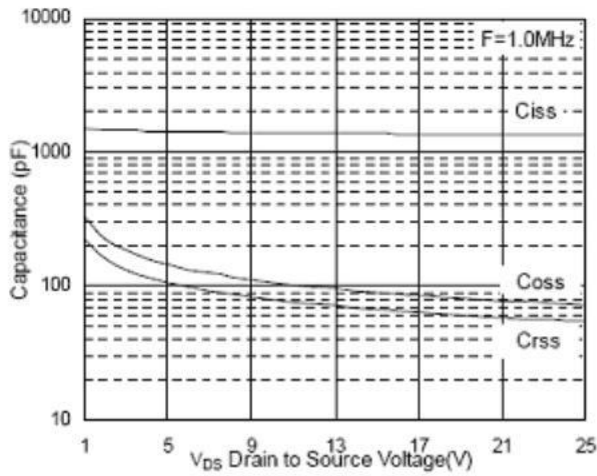


Fig.7 Capacitance

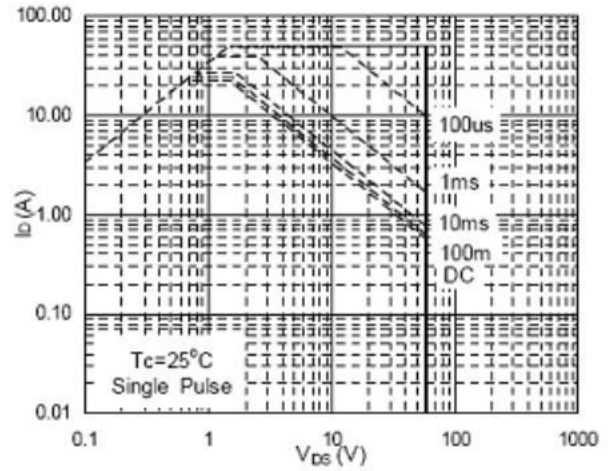


Fig.8 Safe Operating Area

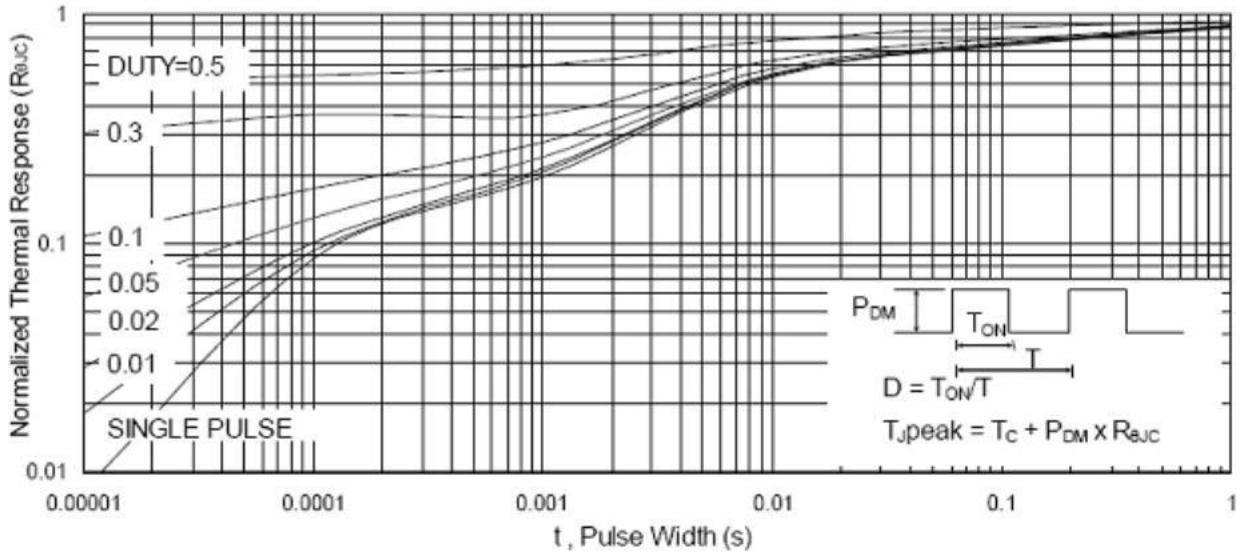


Fig.9 Normalized Maximum Transient Thermal Impedance

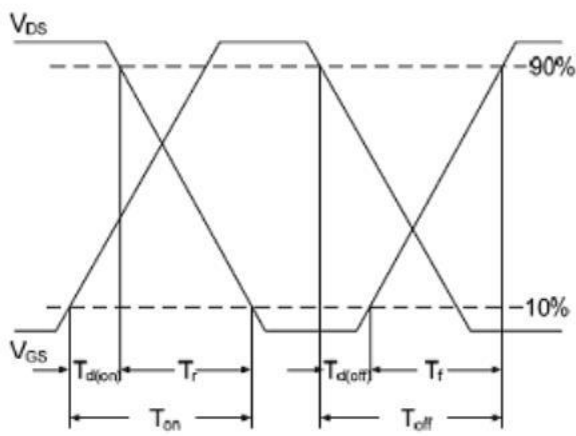


Fig.10 Switching Time Waveform

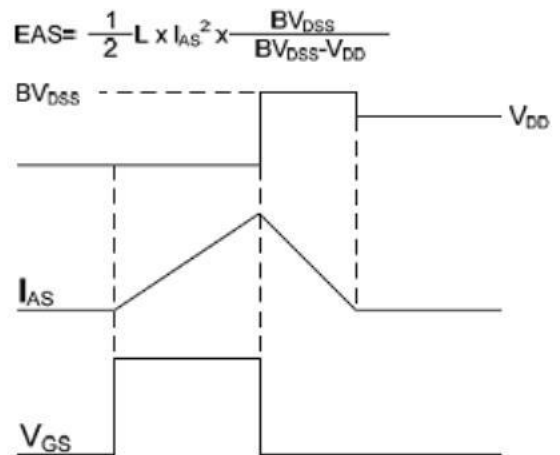


Fig.11 Unclamped Inductive Waveform

$$EAS = \frac{1}{2} L \times I_{AS}^2 \times \frac{BV_{DSS}}{BV_{DSS} - V_{DD}}$$

单击下面可查看定价，库存，交付和生命周期等信息

[>>UMW\(友台半导体\)](#)